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Vishay Siliconix

# Automotive N-Channel 200 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	200	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.035	
I <sub>D</sub> (A)	60	
Configuration	Single	
Package	TO-263	



#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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G <b>o</b> –	
N-Channel MOSFET	o s

PARAMETER PARAMETER	, ,	SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	200	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Ossilia a a Baria Ossala	T <sub>C</sub> = 25 °C	I <sub>D</sub>	60	
Continuous Drain Current	T <sub>C</sub> = 125 °C		35	
Continuous Source Current (Diode Conduction) a		Is	120	А
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	100	
Single Pulse Avalanche Current	. 0.4 11	I <sub>AS</sub>	26	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	33	mJ
	T <sub>C</sub> = 25 °C	_	375	14/
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	125	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>sta</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	0.4	C/VV

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μA	200	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 200 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 200 V, T <sub>J</sub> = 125 °C	-	-	75	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 200 V, T <sub>J</sub> = 175 °C	-	-	2	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	60	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.028	0.035	
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	$I_D = 20 \text{ A}, T_J = 125 ^{\circ}\text{C}$ - $0.074$ $\Omega$			
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.098	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	67	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	4655	5850	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	410	550	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	195	250	
Total Gate Charge <sup>c</sup>	Qg			-	90	135	
Gate-Source Charge c	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 100 \text{ V}, I_{D} = 9 \text{ A}$	-	16	1	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	29	1	
Gate Resistance	$R_g$		f = 1 MHz	0.3	0.8	1.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	20	30	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} =$	100 V, $R_L$ = 11.1 $Ω$	-	40	60	ne
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 9 A$ ,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	35	53	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	- 20 30		30			
Source-Drain Diode Ratings and Chara	icteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	100	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V		-	0.8	1.5	V

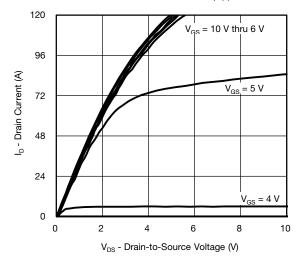
#### Notes

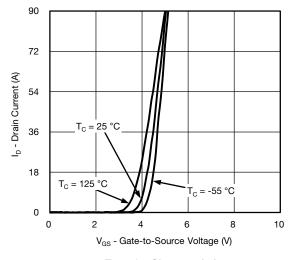
- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

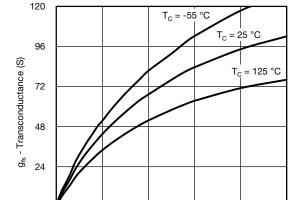


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

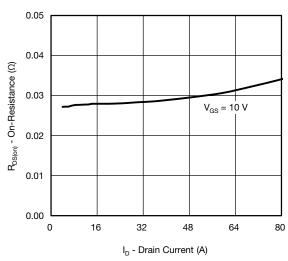




#### **Output Characteristics**



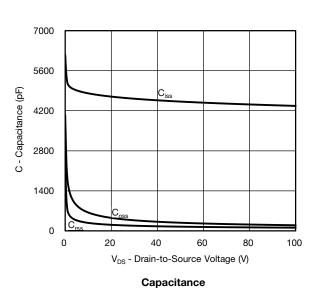
**Transfer Characteristics** 



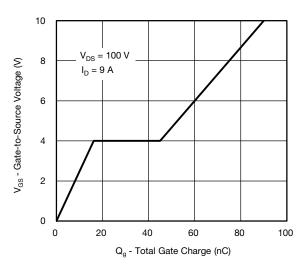
# I<sub>D</sub> - Drain Current (A) **Transconductance**

30

50



On-Resistance vs. Drain Current



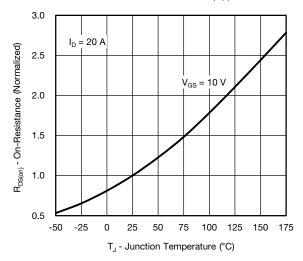
0

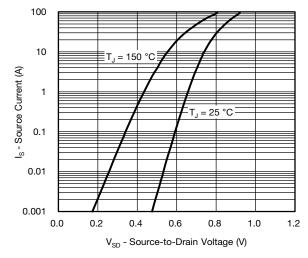
0

10

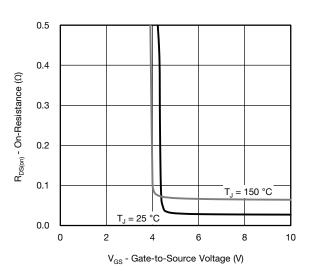


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

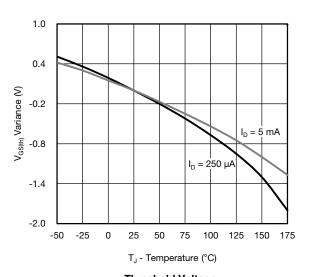




#### On-Resistance vs. Junction Temperature

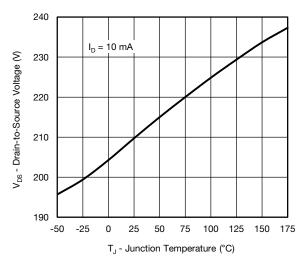


**Source Drain Diode Forward Voltage** 



#### On-Resistance vs. Gate-to-Source Voltage



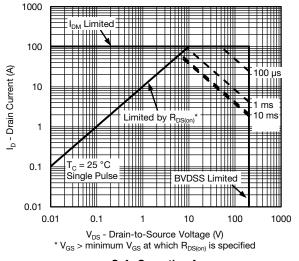


Drain Source Breakdown vs. Junction Temperature

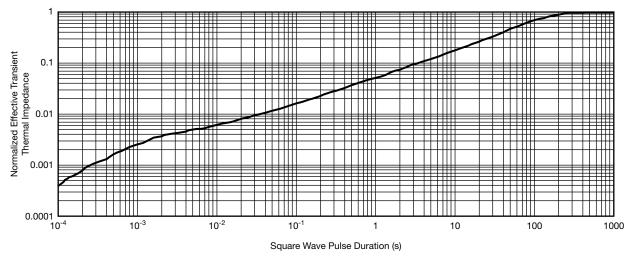
For technical questions, contact: automostechsu



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



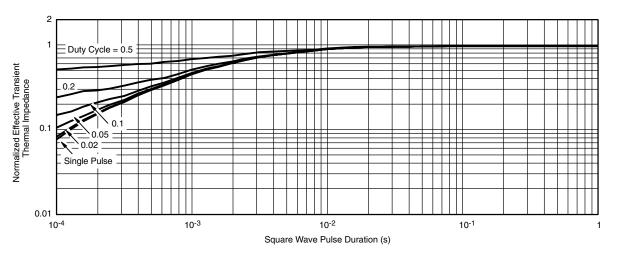
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg262744">www.vishay.com/ppg262744</a>



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REVISION HISTORY a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R <sub>g</sub> minimum limit		

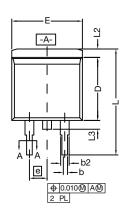
#### Note

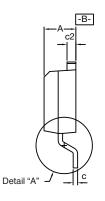
a. As of April 2014

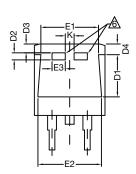
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

### **VERSION 1: FACILITY CODE = T**









**DETAIL A (ROTATED 90°)** 



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SF	CTION	1	1

## **Notes**

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

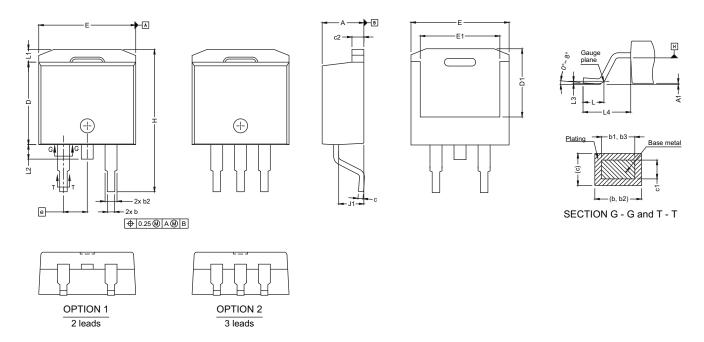
		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
C*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	) BSC	2.54 BSC	
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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## **VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25	5 typ.	
L4	4.78	5.28	
J1	2.56	2.56 2.96	

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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